

L Number	Hits	Search Text	DB	Time stamp
1	520	(CMP or polishing) with (slurry and water)	EPO; JPO; DERWENT; IBM_TDB	2004/08/23 09:19
2	1075183	semiconductor or "integrated circuit"	EPO; JPO; DERWENT; IBM_TDB	2004/08/23 09:19
3	249	((CMP or polishing) with (slurry and water)) and (semiconductor or "integrated circuit")	EPO; JPO; DERWENT; IBM_TDB	2004/08/23 09:24
4	24	438/for.111.ccls.	EPO; JPO; DERWENT; IBM_TDB	2004/08/23 09:24
5	1	((CMP or polishing) with (slurry and water)) and 438/for.111.ccls.	EPO; JPO; DERWENT; IBM_TDB	2004/08/23 09:24
-	1906	438/692.ccls.	USPAT; US-PGPUB	2004/08/19 11:21
-	2943	(CMP or polishing) with (slurry and water)	USPAT; US-PGPUB	2004/08/23 09:18
-	447	438/692.ccls. and ((CMP or polishing) with (slurry and water))	USPAT; US-PGPUB	2004/08/19 10:41
-	439	(438/692.ccls. and ((CMP or polishing) with (slurry and water)))	USPAT; US-PGPUB	2004/08/19 10:45
-	1835	not (@ad>20030901 or @rlad>20030901) (CMP or polishing) with (slurry with water)	USPAT; US-PGPUB	2004/08/19 10:47
-	295	438/692.ccls. and ((CMP or polishing) with (slurry with water))	USPAT; US-PGPUB	2004/08/19 10:47
-	291	(438/692.ccls. and ((CMP or polishing) with (slurry with water))) not (@ad>20030901 or @rlad>20030901)	USPAT; US-PGPUB	2004/08/19 11:10
-	761790	dielectric or insulator or oxide or IMD or FSG or USG or TEOS	USPAT; US-PGPUB	2004/08/19 11:11
-	451	((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS)	USPAT; US-PGPUB	2004/08/19 11:23
-	65	438/692.ccls. and (((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS))	USPAT; US-PGPUB	2004/08/19 11:11
-	65	(438/692.ccls. and (((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS))) not (@ad>20030901 or @rlad>20030901)	USPAT; US-PGPUB	2004/08/19 11:11
-	190	438/750.ccls.	USPAT; US-PGPUB	2004/08/19 11:21
-	0	((((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS)) with 438/750.ccls.	USPAT; US-PGPUB	2004/08/19 11:22
-	357	438/756.ccls.	USPAT; US-PGPUB	2004/08/19 11:21
-	0	((((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS)) with 438/756.ccls.	USPAT; US-PGPUB	2004/08/19 11:21
-	0	((((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS)) same 438/750.ccls.	USPAT; US-PGPUB	2004/08/19 11:22
-	0	((((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS)) and 438/750.ccls.	USPAT; US-PGPUB	2004/08/19 11:22
-	81620	438/\$.ccls.	USPAT; US-PGPUB	2004/08/19 11:23
-	121	((((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS)) and 438/\$.ccls.	USPAT; US-PGPUB	2004/08/19 11:23
-	118	(((((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS)) and 438/\$.ccls.) not (@ad>20030901 or @rlad>20030901)	USPAT; US-PGPUB	2004/08/19 11:23

-	53	(((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS)) and 438/\$.ccls.) not (@ad>20030901 or @rlad>20030901)) not ((438/692.ccls. and (((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS))) not (@ad>20030901 or @rlad>20030901)) semiconductor or "integrated circuit"	USPAT; US-PGPUB	2004/08/19 11:30
-	517047		USPAT; US-PGPUB	2004/08/19 11:30
-	343	(((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS)) and (semiconductor or "integrated circuit")	USPAT; US-PGPUB	2004/08/19 11:31
-	293	(((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS)) and (semiconductor or "integrated circuit")) not (((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS)) and 438/\$.ccls.) not (@ad>20030901 or @rlad>20030901)) not ((438/692.ccls. and (((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS))) not (@ad>20030901 or @rlad>20030901)))	USPAT; US-PGPUB	2004/08/19 11:31
-	237	(((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS)) and (semiconductor or "integrated circuit")) not (((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS)) and 438/\$.ccls.) not (@ad>20030901 or @rlad>20030901)) not ((438/692.ccls. and (((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS))) not (@ad>20030901 or @rlad>20030901))) not ((438/692.ccls. and (((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS))) not (@ad>20030901 or @rlad>20030901)))	USPAT; US-PGPUB	2004/08/19 11:59
-	990	"first polishing" and "second polishing"	USPAT; US-PGPUB	2004/08/19 12:00
-	235	((CMP or polishing) with (slurry with water)) and ("first polishing" and "second polishing")	USPAT; US-PGPUB	2004/08/19 12:00
-	229	(((CMP or polishing) with (slurry with water)) and ("first polishing" and "second polishing")) not (@ad>20030901 or @rlad>20030901)	USPAT; US-PGPUB	2004/08/19 12:00
-	206	(semiconductor or "integrated circuit") and (((CMP or polishing) with (slurry with water)) and ("first polishing" and "second polishing")) not (@ad>20030901 or @rlad>20030901))	USPAT; US-PGPUB	2004/08/19 12:00
-	29	("first polishing" with slurry) and ("second polishing" with water)	USPAT; US-PGPUB	2004/08/19 12:01
-	28	((("first polishing" with slurry) and ("second polishing" with water)) not (@ad>20030901 or @rlad>20030901)	USPAT; US-PGPUB	2004/08/19 12:01
-	139	damascene and (IMD with (FSG or USG or TEOS))	USPAT; US-PGPUB	2004/08/20 11:37
-	56874	@ad>20030901 or @rlad>20030901	USPAT; US-PGPUB	2004/08/20 11:37
-	138	(damascene and (IMD with (FSG or USG or TEOS))) not (@ad>20030901 or @rlad>20030901)	USPAT; US-PGPUB	2004/08/20 11:37
-	260	IMD with (CMP or polishing)	USPAT; US-PGPUB	2004/08/20 11:37
-	45	((damascene and (IMD with (FSG or USG or TEOS))) not (@ad>20030901 or @rlad>20030901)) and (IMD with (CMP or polishing))	USPAT; US-PGPUB	2004/08/21 13:48
-	1	("6255201").PN.	USPAT; US-PGPUB	2004/08/21 13:48